

Description

The G68 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages. This device is suitable for use as a load switching application and a wide variety of other applications.

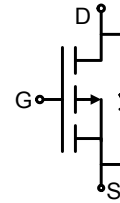
General Features

V_{DSS}	$R_{DS(ON)}$ @ - 4.5V (typ)	I_D
-18V	20m Ω	-7 A

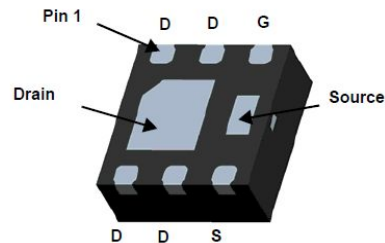
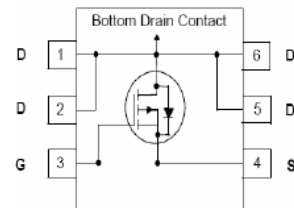
- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge
- RoHS Compliant

Application

- PWM applications
- Load switch
- Battery charge in cellular handset



Schematic diagram



DFN2X2-6L

Ordering Information

Part Number	Marking	Case	Packaging
G68	G68	DFN2*2-6L	3000pcs/Reel

Absolute maximum ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-18	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	-7	A
Drain Current -Pulsed (Note 1)	I_{DM}	-20	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta JC}$	69	$^{\circ}\text{C/W}$
---	-----------------	----	----------------------

Electrical characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR) DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-18	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-12V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-6 A$	-	20	26	m Ω
		$V_{GS}=-2.5V, I_D=-5 A$	-	28	40	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-6A$	-	17	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-9V, V_{GS}=0V,$ $F=1.0MHz$	-	1200	-	PF
Output Capacitance	C_{oss}		-	390	-	PF
Reverse Transfer Capacitance	C_{rss}		-	300	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-6V, I_D=-1A$ $V_{GS}=-4.5V, R_{GEN}=6 \Omega$	-	25	-	nS
Turn-on Rise Time	t_r		-	45	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	72	-	nS
Turn-Off Fall Time	t_f		-	60	-	nS
Total Gate Charge	Q_g	$V_{DS}=-6V, I_D=-6A,$ $V_{GS}=-4.5V$	-	15	48	nC
Gate-Source Charge	Q_{gs}		-	2	-	nC
Gate-Drain Charge	Q_{gd}		-	3.8	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	-7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

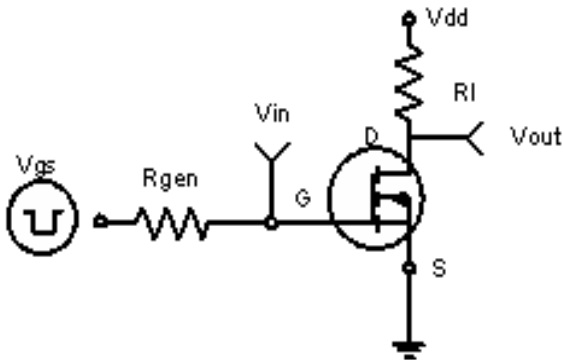


Figure 1: Switching Test Circuit

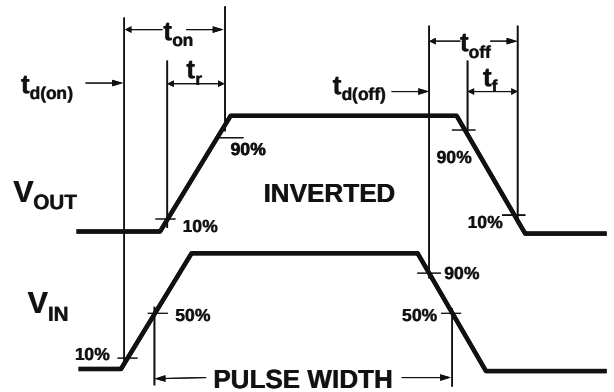


Figure 2: Switching Waveforms

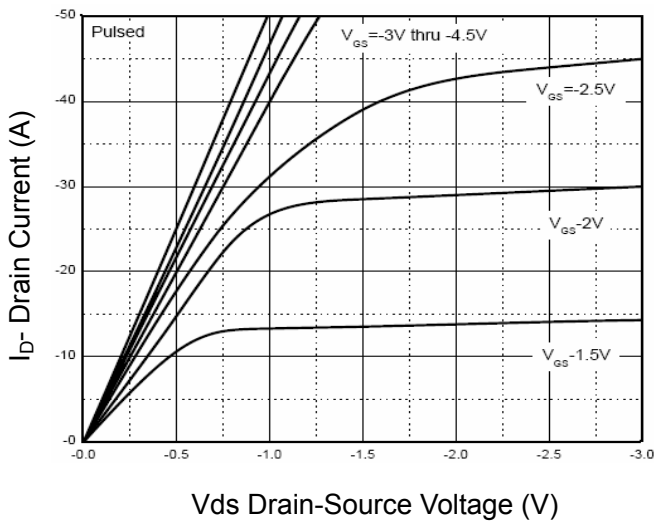


Figure 3 Output Characteristics

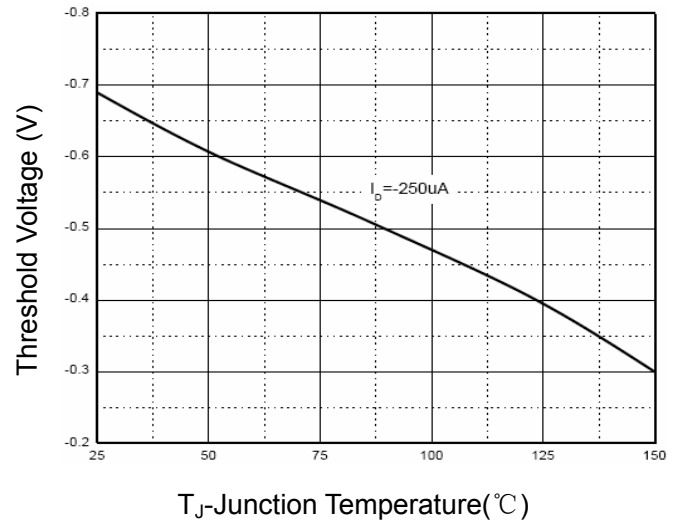


Figure 4 Drain Current

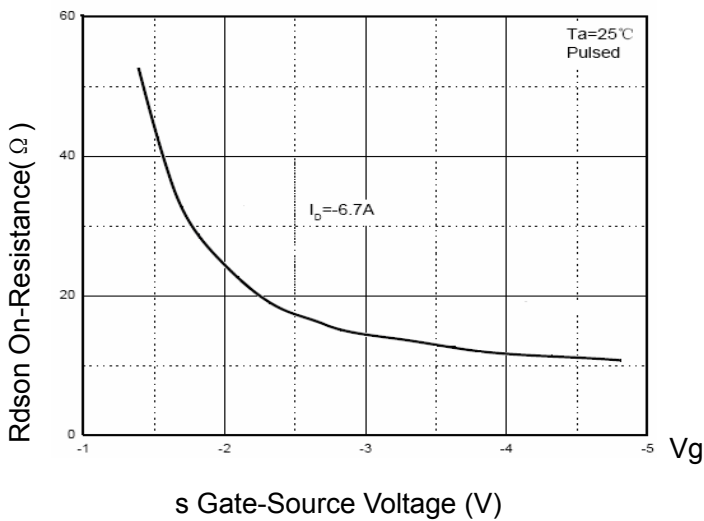


Figure 5 Rdson vs Vgs

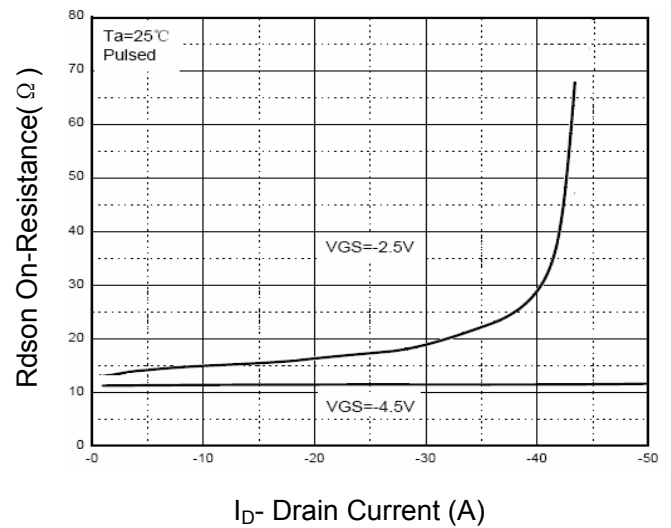
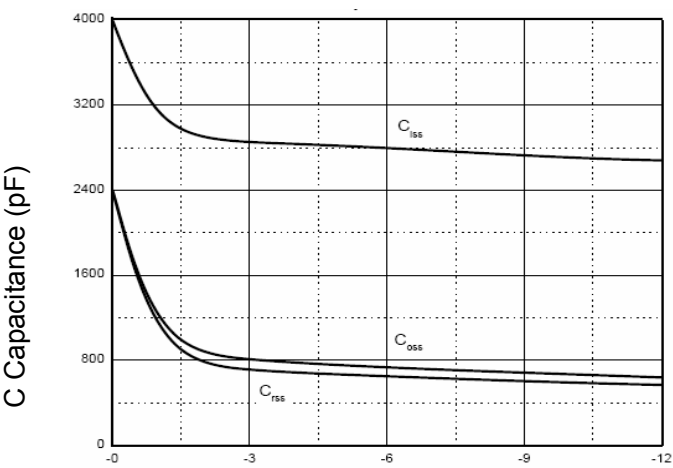
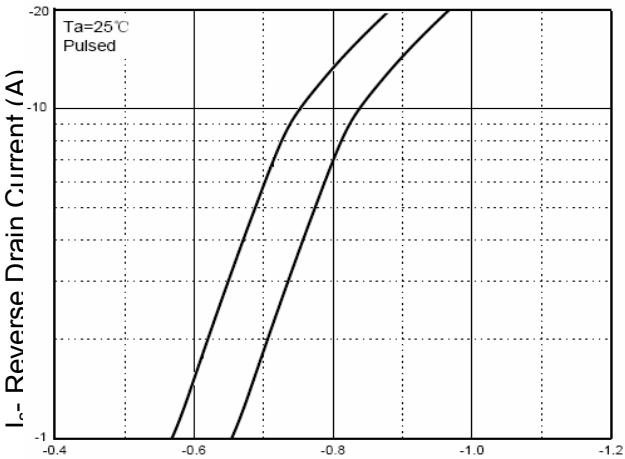


Figure 6 Drain-Source On-Resistance

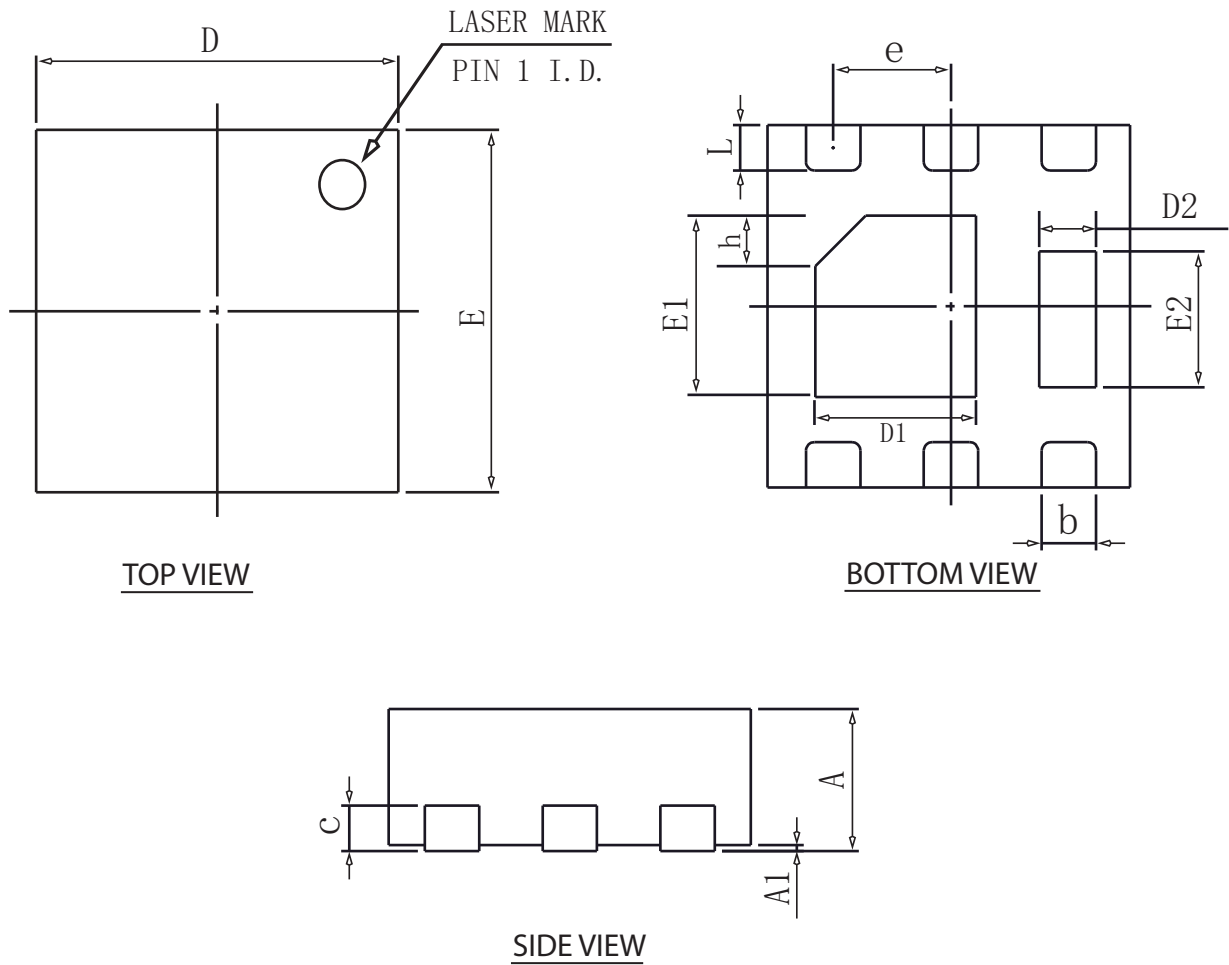


Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



Vsd Source-Drain Voltage (V)
Figure 8 Source- Drain Diode Forward

DFN2X2 Package information



COMMON DIMENSIONS

SYMBOL	mm		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	NA	0.02	0.05
b	0.20	0.27	0.34
c	0.18	0.20	0.25
D	1.95	2.00	2.07
E	1.95	2.00	2.07
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
e	0.65BSC		